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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	625
Number of Logic Elements/Cells	5000
Total RAM Bits	169984
Number of I/O	172
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FTBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfxp2-5e-6ftn256c

LatticeXP2 Family Data Sheet Introduction

February 2012 **Data Sheet DS1009**

Features

- **flexiFLASH™ Architecture**
  - Instant-on
  - Infinitely reconfigurable
  - Single chip
  - FlashBAK™ technology
  - Serial TAG memory
  - Design security
- **Live Update Technology**
  - TransFR™ technology
  - Secure updates with 128 bit AES encryption
  - Dual-boot with external SPI
- **sysDSP™ Block**
  - Three to eight blocks for high performance Multiply and Accumulate
  - 12 to 32 18x18 multipliers
  - Each block supports one 36x36 multiplier or four 18x18 or eight 9x9 multipliers
- **Embedded and Distributed Memory**
  - Up to 885 Kbits sysMEM™ EBR
  - Up to 83 Kbits Distributed RAM
- **sysCLOCK™ PLLs**
  - Up to four analog PLLs per device
  - Clock multiply, divide and phase shifting
- **Flexible I/O Buffer**
  - sysIO™ buffer supports:
    - LVCMOS 33/25/18/15/12; LVTTL
    - SSTL 33/25/18 class I, II
    - HSTL15 class I; HSTL18 class I, II
    - PCI
    - LVDS, Bus-LVDS, MLVDS, LVPECL, RSDS
- **Pre-engineered Source Synchronous Interfaces**
  - DDR / DDR2 interfaces up to 200 MHz
  - 7:1 LVDS interfaces support display applications
  - XGMII
- **Density And Package Options**
  - 5k to 40k LUT4s, 86 to 540 I/Os
  - csBGA, TQFP, PQFP, ftBGA and fpBGA packages
  - Density migration supported
- **Flexible Device Configuration**
  - SPI (master and slave) Boot Flash Interface
  - Dual Boot Image supported
  - Soft Error Detect (SED) macro embedded
- **System Level Support**
  - IEEE 1149.1 and IEEE 1532 Compliant
  - On-chip oscillator for initialization & general use
  - Devices operate with 1.2V power supply

Table 1-1. LatticeXP2 Family Selection Guide

Device	**XP2-5**	**XP2-8**	**XP2-17**	**XP2-30**	**XP2-40**
LUTs (K)	5	8	17	29	40
Distributed RAM (KBits)	10	18	35	56	83
EBR SRAM (KBits)	166	221	276	387	885
EBR SRAM Blocks	9	12	15	21	48
sysDSP Blocks	3	4	5	7	8
18 x 18 Multipliers	12	16	20	28	32
V_{CC} Voltage	1.2	1.2	1.2	1.2	1.2
GPLL	2	2	4	4	4
Max Available I/O	172	201	358	472	540
Packages and I/O Combinations					
132-Ball csBGA (8 x 8 mm)	86	86			
144-Pin TQFP (20 x 20 mm)	100	100			
208-Pin PQFP (28 x 28 mm)	146	146	146		
256-Ball ftBGA (17 x17 mm)	172	201	201	201	
484-Ball fpBGA (23 x 23 mm)			358	363	363
672-Ball fpBGA (27 x 27 mm)				472	540

LatticeXP2 Family Data Sheet
Architecture

August 2014 **Data Sheet DS1009**

Architecture Overview

Each LatticeXP2 device contains an array of logic blocks surrounded by Programmable I/O Cells (PIC). Interspersed between the rows of logic blocks are rows of sysMEM™ Embedded Block RAM (EBR) and a row of sysDSP™ Digital Signal Processing blocks as shown in Figure 2-1.

On the left and right sides of the Programmable Functional Unit (PFU) array, there are Non-volatile Memory Blocks. In configuration mode the nonvolatile memory is programmed via the IEEE 1149.1 TAP port or the sysCONFIG™ peripheral port. On power up, the configuration data is transferred from the Non-volatile Memory Blocks to the configuration SRAM. With this technology, expensive external configuration memory is not required, and designs are secured from unauthorized read-back. This transfer of data from non-volatile memory to configuration SRAM via wide busses happens in microseconds, providing an "instant-on" capability that allows easy interfacing in many applications. LatticeXP2 devices can also transfer data from the sysMEM EBR blocks to the Non-volatile Memory Blocks at user request.

There are two kinds of logic blocks, the PFU and the PFU without RAM (PFF). The PFU contains the building blocks for logic, arithmetic, RAM and ROM functions. The PFF block contains building blocks for logic, arithmetic and ROM functions. Both PFU and PFF blocks are optimized for flexibility allowing complex designs to be implemented quickly and efficiently. Logic Blocks are arranged in a two-dimensional array. Only one type of block is used per row.

LatticeXP2 devices contain one or more rows of sysMEM EBR blocks. sysMEM EBRs are large dedicated 18Kbit memory blocks. Each sysMEM block can be configured in a variety of depths and widths of RAM or ROM. In addition, LatticeXP2 devices contain up to two rows of DSP Blocks. Each DSP block has multipliers and adder/accumulators, which are the building blocks for complex signal processing capabilities.

Each PIC block encompasses two PIOs (PIO pairs) with their respective sysIO buffers. The sysIO buffers of the LatticeXP2 devices are arranged into eight banks, allowing the implementation of a wide variety of I/O standards. PIO pairs on the left and right edges of the device can be configured as LVDS transmit/receive pairs. The PIC logic also includes pre-engineered support to aid in the implementation of high speed source synchronous standards such as 7:1 LVDS interfaces, found in many display applications, and memory interfaces including DDR and DDR2.

The LatticeXP2 registers in PFU and sysI/O can be configured to be SET or RESET. After power up and device is configured, the device enters into user mode with these registers SET/RESET according to the configuration setting, allowing device entering to a known state for predictable system function.

Other blocks provided include PLLs and configuration functions. The LatticeXP2 architecture provides up to four General Purpose PLLs (GPLL) per device. The GPLL blocks are located in the corners of the device.

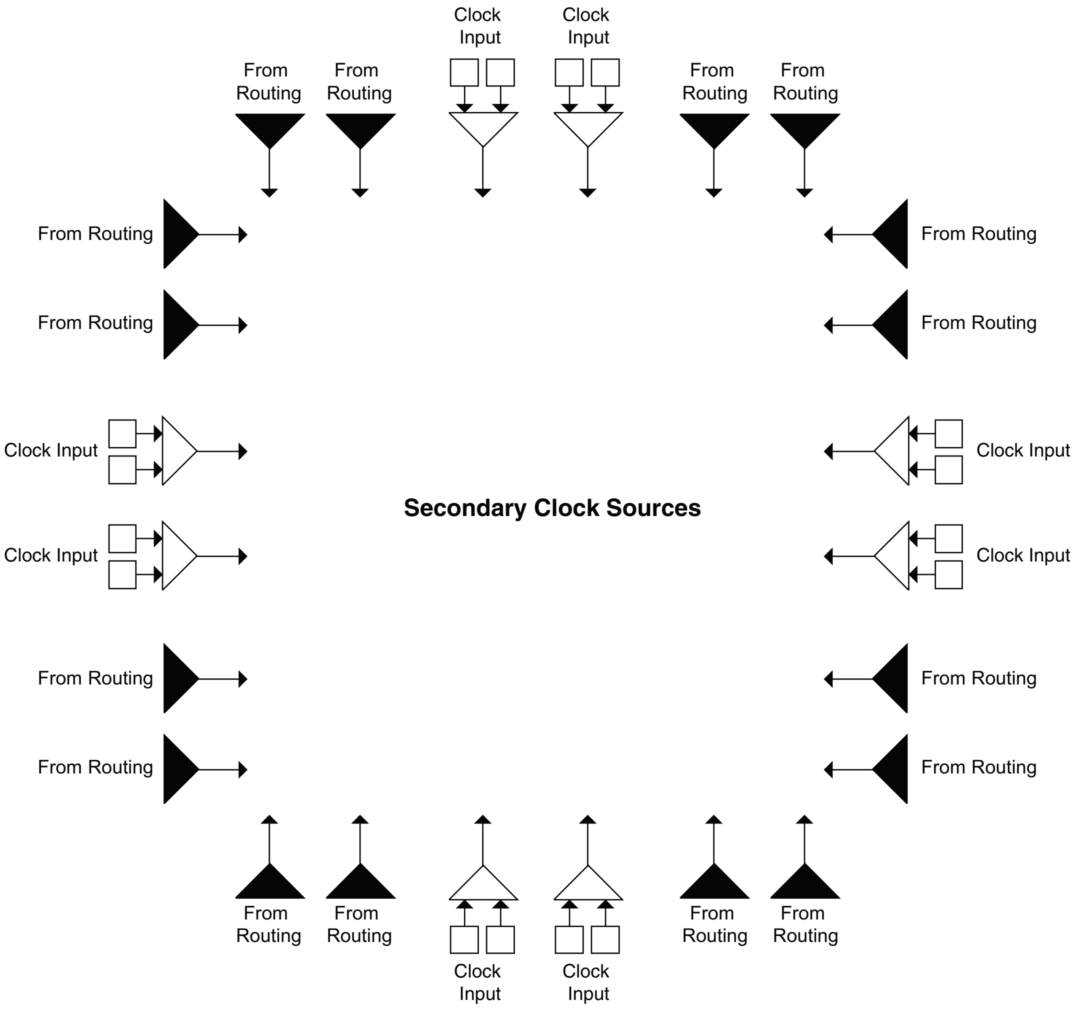
The configuration block that supports features such as configuration bit-stream de-encryption, transparent updates and dual boot support is located between banks two and three. Every device in the LatticeXP2 family supports a sysCONFIG port, muxed with bank seven I/Os, which supports serial device configuration. A JTAG port is provided between banks two and three.

This family also provides an on-chip oscillator. LatticeXP2 devices use 1.2V as their core voltage.

Secondary Clock/Control Sources

LatticeXP2 devices derive secondary clocks (SC0 through SC7) from eight dedicated clock input pads and the rest from routing. Figure 2-7 shows the secondary clock sources.

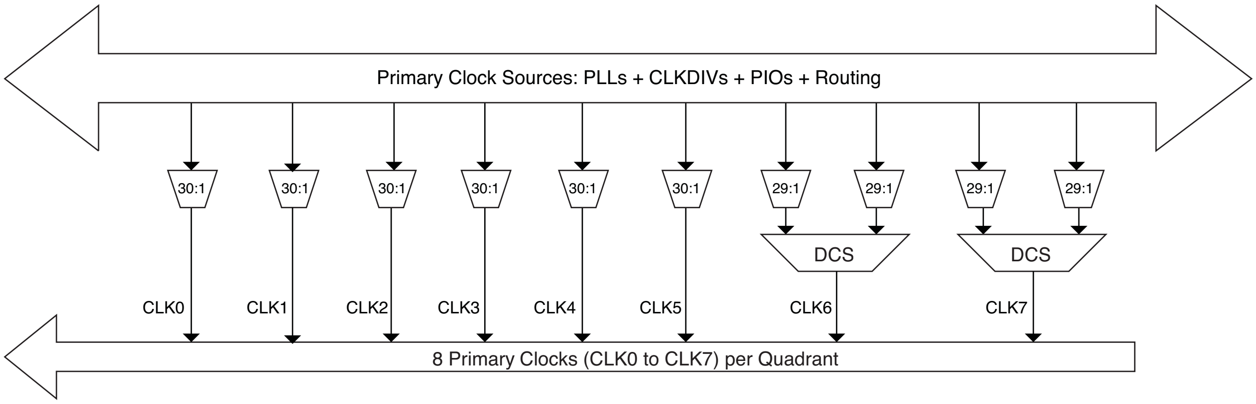
Figure 2-7. Secondary Clock Sources



Primary Clock Routing

The clock routing structure in LatticeXP2 devices consists of a network of eight primary clock lines (CLK0 through CLK7) per quadrant. The primary clocks of each quadrant are generated from muxes located in the center of the device. All the clock sources are connected to these muxes. Figure 2-9 shows the clock routing for one quadrant. Each quadrant mux is identical. If desired, any clock can be routed globally.

Figure 2-9. Per Quadrant Primary Clock Selection

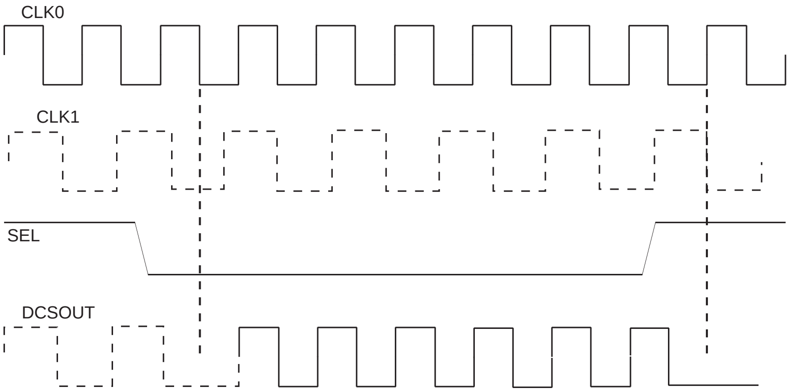


Dynamic Clock Select (DCS)

The DCS is a smart multiplexer function available in the primary clock routing. It switches between two independent input clock sources without any glitches or runt pulses. This is achieved irrespective of when the select signal is toggled. There are two DCS blocks per quadrant; in total, eight DCS blocks per device. The inputs to the DCS block come from the center muxes. The output of the DCS is connected to primary clocks CLK6 and CLK7 (see Figure 2-9).

Figure 2-10 shows the timing waveforms of the default DCS operating mode. The DCS block can be programmed to other modes. For more information on the DCS, please see TN1126, LatticeXP2 sysCLOCK PLL Design and Usage Guide.

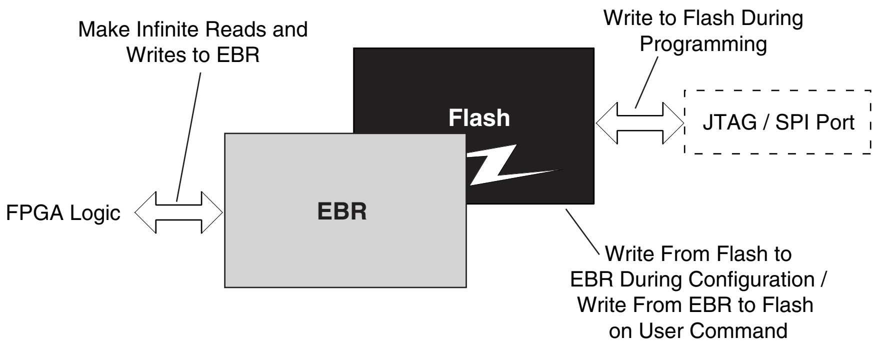
Figure 2-10. DCS Waveforms



Secondary Clock/Control Routing

Secondary clocks in the LatticeXP2 devices are region-based resources. The benefit of region-based resources is the relatively low injection delay and skew within the region, as compared to primary clocks. EBR rows, DSP rows and a special vertical routing channel bound the secondary clock regions. This special vertical routing channel aligns with either the left edge of the center DSP block in the DSP row or the center of the DSP row. Figure 2-11 shows this special vertical routing channel and the eight secondary clock regions for the LatticeXP2-40.

Figure 2-16. FlashBAK Technology



Memory Cascading

Larger and deeper blocks of RAMs can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

Single, Dual and Pseudo-Dual Port Modes

In all the sysMEM RAM modes the input data and address for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the output.

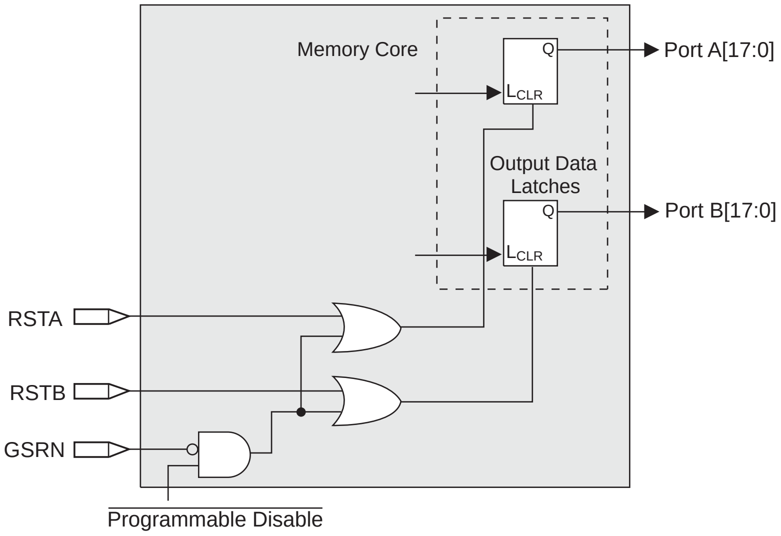
EBR memory supports two forms of write behavior for single port or dual port operation:

1. Normal – Data on the output appears only during a read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.
2. Write Through – A copy of the input data appears at the output of the same port during a write cycle. This mode is supported for all data widths.

Memory Core Reset

The memory array in the EBR utilizes latches at the A and B output ports. These latches can be reset asynchronously or synchronously. RSTA and RSTB are local signals, which reset the output latches associated with Port A and Port B respectively. GSRN, the global reset signal, resets both ports. The output data latches and associated resets for both ports are as shown in Figure 2-17.

Figure 2-17. Memory Core Reset

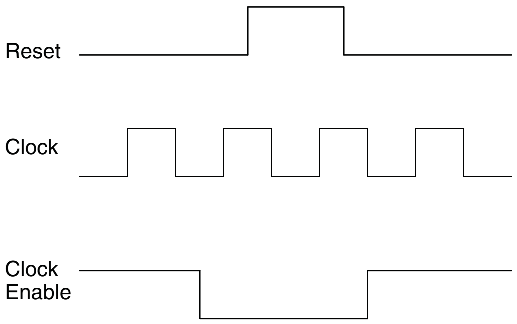


For further information on the sysMEM EBR block, please see TN1137, LatticeXP2 Memory Usage Guide.

EBR Asynchronous Reset

EBR asynchronous reset or GSR (if used) can only be applied if all clock enables are low for a clock cycle before the reset is applied and released a clock cycle after the low-to-high transition of the reset signal, as shown in Figure 2-18. The GSR input to the EBR is always asynchronous.

Figure 2-18. EBR Asynchronous Reset (Including GSR) Timing Diagram



If all clock enables remain enabled, the EBR asynchronous reset or GSR may only be applied and released after the EBR read and write clock inputs are in a steady state condition for a minimum of $1/f_{MAX}$ (EBR clock). The reset release must adhere to the EBR synchronous reset setup time before the next active read or write clock edge.

If an EBR is pre-loaded during configuration, the GSR input must be disabled or the release of the GSR during device Wake Up must occur before the release of the device I/Os becoming active.

These instructions apply to all EBR RAM and ROM implementations.

Note that there are no reset restrictions if the EBR synchronous reset is used and the EBR GSR input is disabled.

sysDSP™ Block

The LatticeXP2 family provides a sysDSP block making it ideally suited for low cost, high performance Digital Signal Processing (DSP) applications. Typical functions used in these applications include Bit Correlators, Fast Fourier Transform (FFT) functions, Finite Impulse Response (FIR) Filter, Reed-Solomon Encoder/Decoder, Turbo Encoder/Decoder and Convolutional Encoder/Decoder. These complex signal processing functions use similar building blocks such as multiply-adders and multiply-accumulators.

sysDSP Block Approach Compare to General DSP

Conventional general-purpose DSP chips typically contain one to four (Multiply and Accumulate) MAC units with fixed data-width multipliers; this leads to limited parallelism and limited throughput. Their throughput is increased by higher clock speeds. The LatticeXP2 family, on the other hand, has many DSP blocks that support different data-widths. This allows the designer to use highly parallel implementations of DSP functions. The designer can optimize the DSP performance vs. area by choosing appropriate levels of parallelism. Figure 2-19 compares the fully serial and the mixed parallel and serial implementations.

MAC sysDSP Element

In this case, the two operands, A and B, are multiplied and the result is added with the previous accumulated value. This accumulated value is available at the output. The user can enable the input and pipeline registers but the output register is always enabled. The output register is used to store the accumulated value. The Accumulators in the DSP blocks in LatticeXP2 family can be initialized dynamically. A registered overflow signal is also available. The overflow conditions are provided later in this document. Figure 2-21 shows the MAC sysDSP element.

Figure 2-21. MAC sysDSP

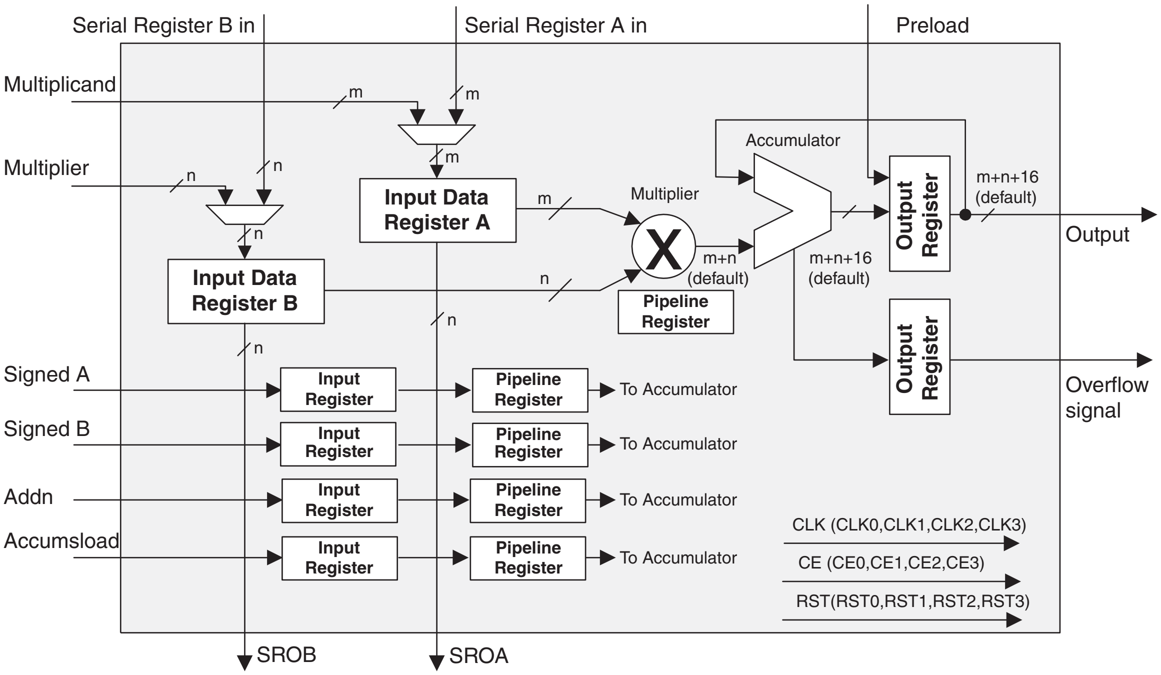


Table 2-11. PIO Signal List

Name	Type	Description
CE	Control from the core	Clock enables for input and output block flip-flops
CLK	Control from the core	System clocks for input and output blocks
ECLK1, ECLK2	Control from the core	Fast edge clocks
LSR	Control from the core	Local Set/Reset
GSRN	Control from routing	Global Set/Reset (active low)
INCK[2]	Input to the core	Input to Primary Clock Network or PLL reference inputs
DQS	Input to PIO	DQS signal from logic (routing) to PIO
INDD	Input to the core	Unregistered data input to core
INFF	Input to the core	Registered input on positive edge of the clock (CLK0)
IPOS0, IPOS1	Input to the core	Double data rate registered inputs to the core
QPOS0[1], QPOS1[1]	Input to the core	Gearbox pipelined inputs to the core
QNEG0[1], QNEG1[1]	Input to the core	Gearbox pipelined inputs to the core
OPOS0, ONEG0, OPOS2, ONEG2	Output data from the core	Output signals from the core for SDR and DDR operation
OPOS1 ONEG1	Tristate control from the core	Signals to Tristate Register block for DDR operation
DEL[3:0]	Control from the core	Dynamic input delay control bits
TD	Tristate control from the core	Tristate signal from the core used in SDR operation
DDRCLKPOL	Control from clock polarity bus	Controls the polarity of the clock (CLK0) that feed the DDR input block
DQSXFER	Control from core	Controls signal to the Output block

1. Signals available on left/right/bottom only.
2. Selected I/O.

PIO

The PIO contains four blocks: an input register block, output register block, tristate register block and a control logic block. These blocks contain registers for operating in a variety of modes along with necessary clock and selection logic.

Input Register Block

The input register blocks for PIOs contain delay elements and registers that can be used to condition high-speed interface signals, such as DDR memory interfaces and source synchronous interfaces, before they are passed to the device core. Figure 2-26 shows the diagram of the input register block.

Input signals are fed from the sysIO buffer to the input register block (as signal DI). If desired, the input signal can bypass the register and delay elements and be used directly as a combinatorial signal (INDD), a clock (INCK) and, in selected blocks, the input to the DQS delay block. If an input delay is desired, designers can select either a fixed delay or a dynamic delay DEL[3:0]. The delay, if selected, reduces input register hold time requirements when using a global clock.

The input block allows three modes of operation. In the Single Data Rate (SDR) mode, the data is registered, by one of the registers in the SDR Sync register block, with the system clock. In DDR mode two registers are used to sample the data on the positive and negative edges of the DQS signal which creates two data streams, D0 and D2. D0 and D2 are synchronized with the system clock before entering the core. Further information on this topic can be found in the DDR Memory Support section of this data sheet.

By combining input blocks of the complementary PIOs and sharing registers from output blocks, a gearbox function can be implemented, that takes a double data rate signal applied to PIOA and converts it as four data streams, IPOS0A, IPOS1A, IPOS0B and IPOS1B. Figure 2-26 shows the diagram using this gearbox function. For more information on this topic, please see TN1138, LatticeXP2 High Speed I/O Interface.

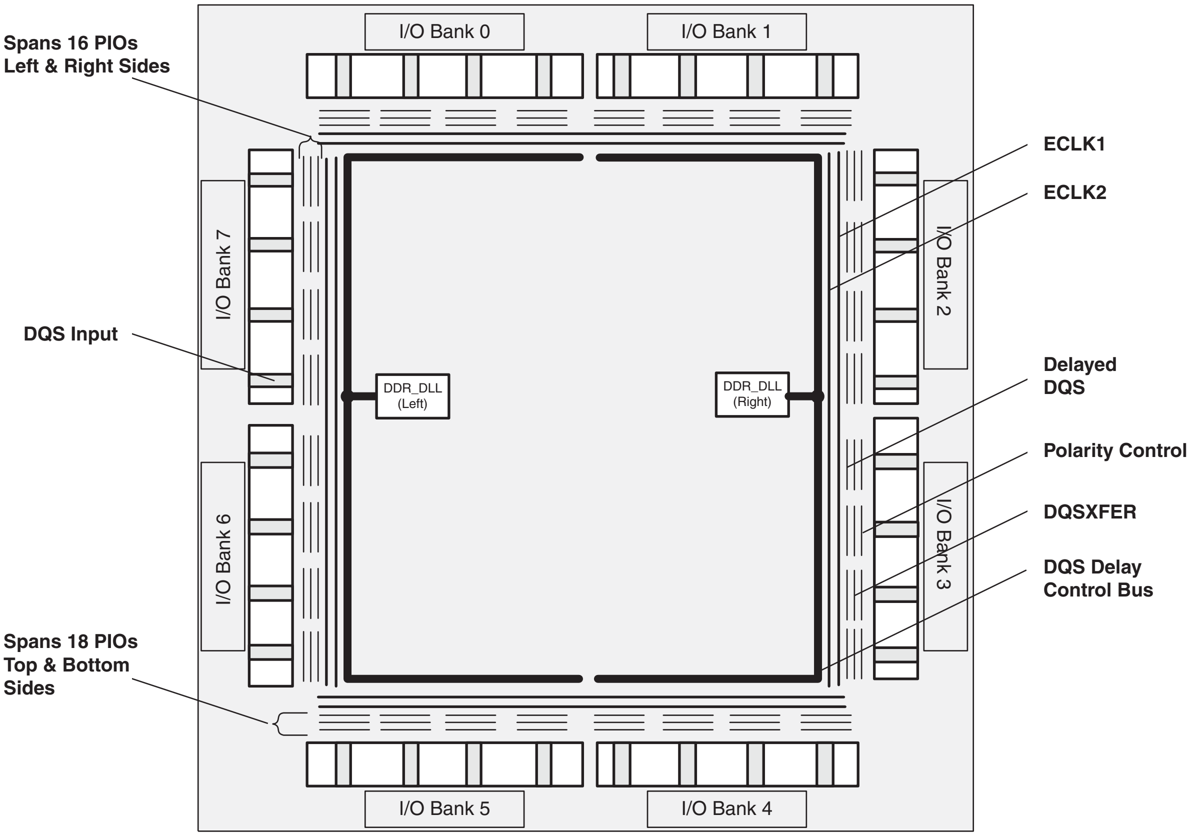
DLL Calibrated DQS Delay Block

Source synchronous interfaces generally require the input clock to be adjusted in order to correctly capture data at the input register. For most interfaces a PLL is used for this adjustment. However, in DDR memories the clock, referred to as DQS, is not free-running, and this approach cannot be used. The DQS Delay block provides the required clock alignment for DDR memory interfaces.

The DQS signal (selected PIOs only, as shown in Figure 2-30) feeds from the PAD through a DQS delay element to a dedicated DQS routing resource. The DQS signal also feeds polarity control logic which controls the polarity of the clock to the sync registers in the input register blocks. Figure 2-30 and Figure 2-31 show how the DQS transition signals are routed to the PIOs.

The temperature, voltage and process variations of the DQS delay block are compensated by a set of 6-bit bus calibration signals from two dedicated DLLs (DDR_DLL) on opposite sides of the device. Each DLL compensates DQS delays in its half of the device as shown in Figure 2-30. The DLL loop is compensated for temperature, voltage and process variations by the system clock and feedback loop.

Figure 2-30. Edge Clock, DLL Calibration and DQS Local Bus Distribution

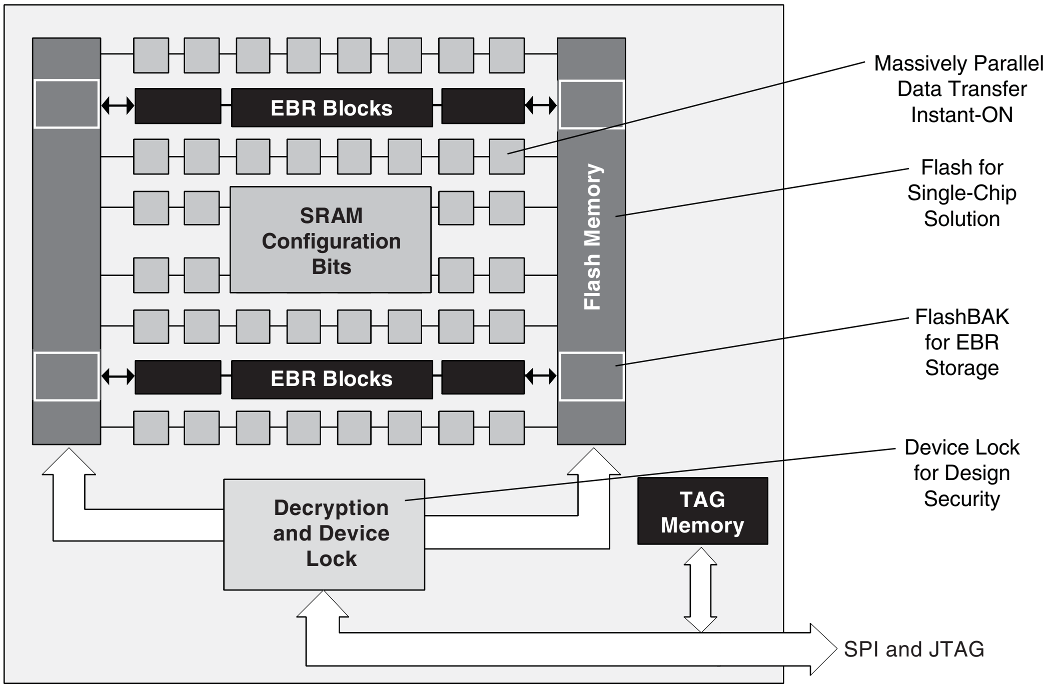


and loaded directly onto test nodes, or test data to be captured and shifted out for verification. The test access port consists of dedicated I/Os: TDI, TDO, TCK and TMS. The test access port has its own supply voltage V_{CCJ} and can operate with LVCMOS3.3, 2.5, 1.8, 1.5 and 1.2 standards. For more information, please see TN1141, LatticeXP2 sysCONFIG Usage Guide.

flexiFLASH Device Configuration

The LatticeXP2 devices combine Flash and SRAM on a single chip to provide users with flexibility in device programming and configuration. Figure 2-33 provides an overview of the arrangement of Flash and SRAM configuration cells within the device. The remainder of this section provides an overview of these capabilities. See TN1141, LatticeXP2 sysCONFIG Usage Guide for a more detailed description.

Figure 2-33. Overview of Flash and SRAM Configuration Cells Within LatticeXP2 Devices



At power-up, or on user command, data is transferred from the on-chip Flash memory to the SRAM configuration cells that control the operation of the device. This is done with massively parallel buses enabling the parts to operate within microseconds of the power supplies reaching valid levels; this capability is referred to as Instant-On.

The on-chip Flash enables a single-chip solution eliminating the need for external boot memory. This Flash can be programmed through either the JTAG or Slave SPI ports of the device. The SRAM configuration space can also be infinitely reconfigured through the JTAG and Master SPI ports. The JTAG port is IEEE 1149.1 and IEEE 1532 compliant.

As described in the EBR section of the data sheet, the FlashBAK capability of the parts enables the contents of the EBR blocks to be written back into the Flash storage area without erasing or reprogramming other aspects of the device configuration. Serial TAG memory is also available to allow the storage of small amounts of data such as calibration coefficients and error codes.

For applications where security is important, the lack of an external bitstream provides a solution that is inherently more secure than SRAM only FPGAs. This is further enhanced by device locking. The device can be in one of three modes:

LatticeXP2 Family Data Sheet
DC and Switching Characteristics

September 2014 **Data Sheet DS1009**

Absolute Maximum Ratings[1, 2, 3]

Supply Voltage V_{CC} . . . . -0.5 to 1.32V

Supply Voltage V_{CCAUX} . . . . -0.5 to 3.75V

Supply Voltage V_{CCJ} . . . . -0.5 to 3.75V

Supply Voltage V_{CCPLL}[4]. . . . . -0.5 to 3.75V

Output Supply Voltage V_{CCIO} . . . . -0.5 to 3.75V

Input or I/O Tristate Voltage Applied[5]. . . . . . -0.5 to 3.75V

Storage Temperature (Ambient) . . . . -65 to 150°C

Junction Temperature Under Bias (Tj). . . . . +125°C

1. Stress above those listed under the “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice Thermal Management document is required.
3. All voltages referenced to GND.
4. V_{CCPLL} only available on csBGA, PQFP and TQFP packages.
5. Overshoot and undershoot of -2V to (V_{IHMAX} + 2) volts is permitted for a duration of <20 ns.

Recommended Operating Conditions

Symbol	Parameter	Min.	Max.	Units
V_{CC}	Core Supply Voltage	1.14	1.26	V
V_{CCAUX}[4, 5]	Auxiliary Supply Voltage	3.135	3.465	V
V_{CCPLL}[1]	PLL Supply Voltage	3.135	3.465	V
V_{CCIO}[2, 3, 4]	I/O Driver Supply Voltage	1.14	3.465	V
V_{CCJ}[2]	Supply Voltage for IEEE 1149.1 Test Access Port	1.14	3.465	V
t_{JCOM}	Junction Temperature, Commercial Operation	0	85	°C
t_{JIND}	Junction Temperature, Industrial Operation	-40	100	°C

1. V_{CCPLL} only available on csBGA, PQFP and TQFP packages.
2. If V_{CCIO} or V_{CCJ} is set to 1.2 V, they must be connected to the same power supply as $V_{CC.}$ If V_{CCIO} or V_{CCJ} is set to 3.3V, they must be connected to the same power supply as V_{CCAUX}.
3. See recommended voltages by I/O standard in subsequent table.
4. To ensure proper I/O behavior, V_{CCIO} must be turned off at the same time or earlier than $V_{CCAUX.}$
5. In fpBGA and ftBGA packages, the PLLs are connected to, and powered from, the auxiliary power supply.

On-Chip Flash Memory Specifications

Symbol	Parameter	Max.	Units
$N_{PROGCYC}$	Flash Programming Cycles per $t_{RETENTION}$[1]	10,000	Cycles
	Flash Functional Programming Cycles	100,000	

1. The minimum data retention, $t_{RETENTION}$, is 20 years.

sysIO Recommended Operating Conditions

Over Recommended Operating Conditions

Standard	V_{CCIO}			V_{REF} (V)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
LVCMOS33[2]	3.135	3.3	3.465	—	—	—
LVCMOS25[2]	2.375	2.5	2.625	—	—	—
LVCMOS18	1.71	1.8	1.89	—	—	—
LVCMOS15	1.425	1.5	1.575	—	—	—
LVCMOS12[2]	1.14	1.2	1.26	—	—	—
LVTTL33[2]	3.135	3.3	3.465	—	—	—
PCI33	3.135	3.3	3.465	—	—	—
SSTL18_I[2], SSTL18_II[2]	1.71	1.8	1.89	0.833	0.9	0.969
SSTL25_I[2], SSTL25_II[2]	2.375	2.5	2.625	1.15	1.25	1.35
SSTL33_I[2], SSTL33_II[2]	3.135	3.3	3.465	1.3	1.5	1.7
HSTL15_I[2]	1.425	1.5	1.575	0.68	0.75	0.9
HSTL18_I[2], HSTL18_II[2]	1.71	1.8	1.89	0.816	0.9	1.08
LVDS25[2]	2.375	2.5	2.625	—	—	—
MLVDS25[1]	2.375	2.5	2.625	—	—	—
LVPECL33[1, 2]	3.135	3.3	3.465	—	—	—
BLVDS25[1, 2]	2.375	2.5	2.625	—	—	—
RSDS[1, 2]	2.375	2.5	2.625	—	—	—
SSTL18D_I[2], SSTL18D_II[2]	1.71	1.8	1.89	—	—	—
SSTL25D_ I[2], SSTL25D_II[2]	2.375	2.5	2.625	—	—	—
SSTL33D_ I[2], SSTL33D_ II[2]	3.135	3.3	3.465	—	—	—
HSTL15D_ I[2]	1.425	1.5	1.575	—	—	—
HSTL18D_ I[2], HSTL18D_ II[2]	1.71	1.8	1.89	—	—	—

1. Inputs on chip. Outputs are implemented with the addition of external resistors.
2. Input on this standard does not depend on the value of V_{CCIO}.

sysIO Differential Electrical Characteristics

LVDS

Over Recommended Operating Conditions

Parameter	Description	Test Conditions	Min.	Typ.	Max.	Units
V_{INP}, V_{INM}	Input Voltage		0	—	2.4	V
V_{CM}	Input Common Mode Voltage	Half the Sum of the Two Inputs	0.05	—	2.35	V
V_{THD}	Differential Input Threshold	Difference Between the Two Inputs	+/-100	—	—	mV
I_{IN}	Input Current	Power On or Power Off	—	—	+/-10	µA
V_{OH}	Output High Voltage for V_{OP} or V_{OM}	R_T = 100 Ohm	—	1.38	1.60	V
V_{OL}	Output Low Voltage for V_{OP} or V_{OM}	R_T = 100 Ohm	0.9V	1.03	—	V
V_{OD}	Output Voltage Differential	(V_{OP} - V_{OM}), R_T = 100 Ohm	250	350	450	mV
ΔV_{OD}	Change in V_{OD} Between High and Low		—	—	50	mV
V_{OS}	Output Voltage Offset	(V_{OP} + V_{OM})/2, R_T = 100 Ohm	1.125	1.20	1.375	V
ΔV_{OS}	Change in V_{OS} Between H and L		—	—	50	mV
I_{SA}	Output Short Circuit Current	V_{OD} = 0V Driver Outputs Shorted to Ground	—	—	24	mA
I_{SAB}	Output Short Circuit Current	V_{OD} = 0V Driver Outputs Shorted to Each Other	—	—	12	mA

Differential HSTL and SSTL

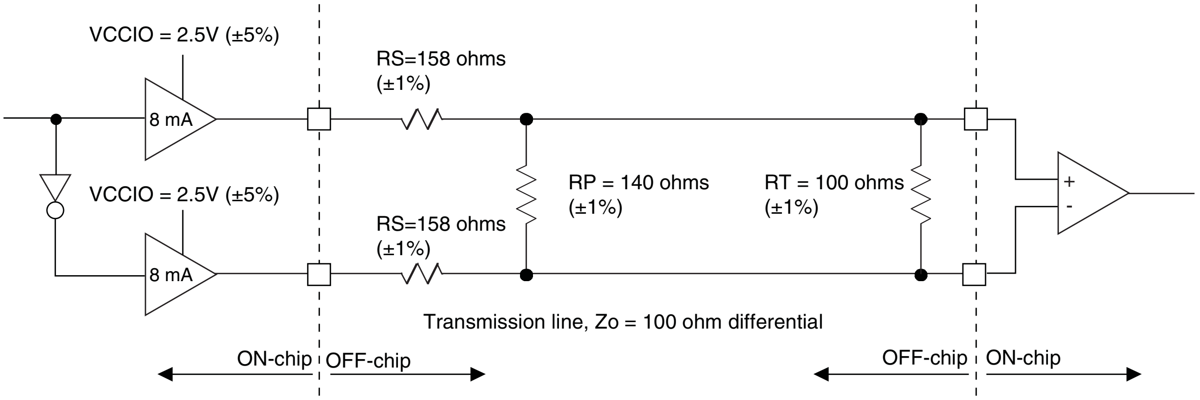
Differential HSTL and SSTL outputs are implemented as a pair of complementary single-ended outputs. All allowable single-ended output classes (class I and class II) are supported in this mode.

For further information on LVPECL, RSDS, MLVDS, BLVDS and other differential interfaces please see details in additional technical notes listed at the end of this data sheet.

LVDS25E

The top and bottom sides of LatticeXP2 devices support LVDS outputs via emulated complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The scheme shown in Figure 3-1 is one possible solution for point-to-point signals.

Figure 3-1. LVDS25E Output Termination Example



BLVDS

The LatticeXP2 devices support the BLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel external resistor across the driver outputs. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.

Figure 3-2. BLVDS Multi-point Output Example

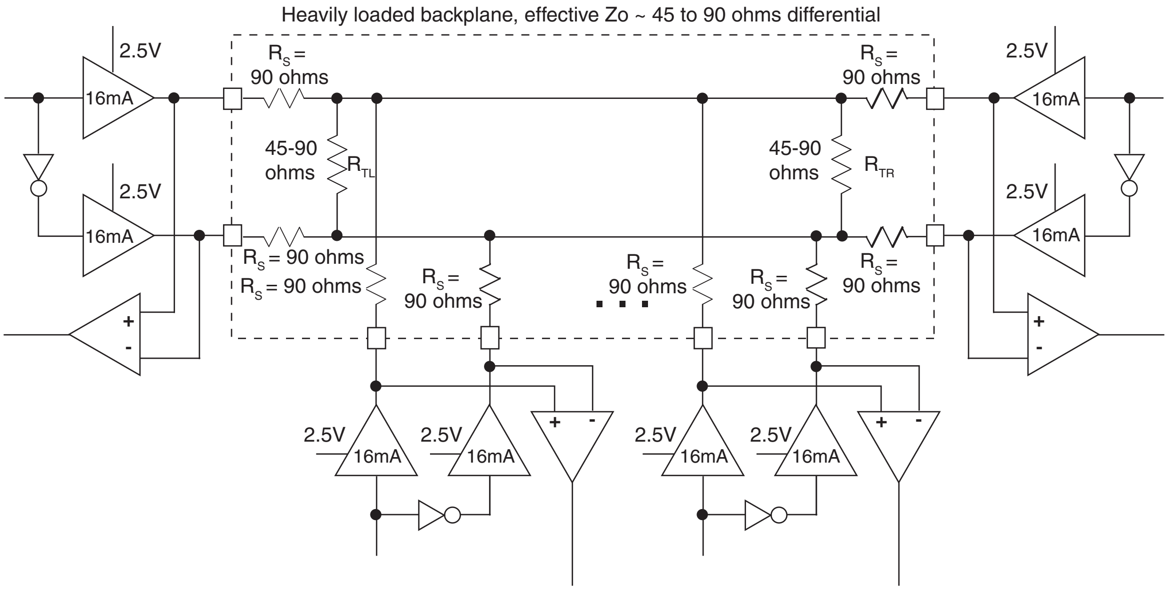


Table 3-2. BLVDS DC Conditions[1]

Over Recommended Operating Conditions

Parameter	Description	Typical		Units
		Zo = 45Ω	Zo = 90Ω	
V_{CCIO}	Output Driver Supply (+/- 5%)	2.50	2.50	V
Z_{OUT}	Driver Impedance	10.00	10.00	Ω
R_S	Driver Series Resistor (+/- 1%)	90.00	90.00	Ω
R_{TL}	Driver Parallel Resistor (+/- 1%)	45.00	90.00	Ω
R_{TR}	Receiver Termination (+/- 1%)	45.00	90.00	Ω
V_{OH}	Output High Voltage (After R_{TL})	1.38	1.48	V
V_{OL}	Output Low Voltage (After R_{TL})	1.12	1.02	V
V_{OD}	Output Differential Voltage (After R_{TL})	0.25	0.46	V
V_{CM}	Output Common Mode Voltage	1.25	1.25	V
I_{DC}	DC Output Current	11.24	10.20	mA

1. For input buffer, see LVDS table.

MLVDS

The LatticeXP2 devices support the differential MLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The MLVDS input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-5 is one possible solution for MLVDS standard implementation. Resistor values in Figure 3-5 are industry standard values for 1% resistors.

Figure 3-5. MLVDS (Reduced Swing Differential Standard)

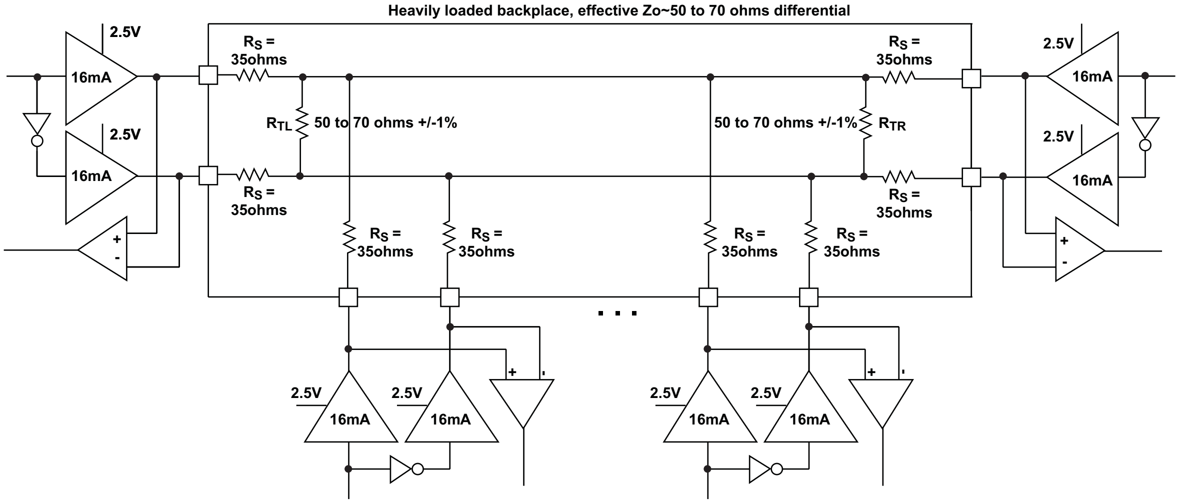


Table 3-5. MLVDS DC Conditions[1]

Parameter	Description	Typical		Units
		Zo=50Ω	Zo=70Ω	
V_{CCIO}	Output Driver Supply (+/-5%)	2.50	2.50	V
Z_{OUT}	Driver Impedance	10.00	10.00	Ω
R_S	Driver Series Resistor (+/-1%)	35.00	35.00	Ω
R_{TL}	Driver Parallel Resistor (+/-1%)	50.00	70.00	Ω
R_{TR}	Receiver Termination (+/-1%)	50.00	70.00	Ω
V_{OH}	Output High Voltage (After R_{TL})	1.52	1.60	V
V_{OL}	Output Low Voltage (After R_{TL})	0.98	0.90	V
V_{OD}	Output Differential Voltage (After R_{TL})	0.54	0.70	V
V_{CM}	Output Common Mode Voltage	1.25	1.25	V
I_{DC}	DC Output Current	21.74	20.00	mA

1. For input buffer, see LVDS table.

For further information on LVPECL, RSDS, MLVDS, BLVDS and other differential interfaces please see details of additional technical information at the end of this data sheet.

LatticeXP2 Family Timing Adders[1, 2, 3, 4] (Continued)

Over Recommended Operating Conditions

Buffer Type	Description	-7	-6	-5	Units
HSTL15_I	HSTL_15 class I 4mA drive	0.32	0.69	1.06	ns
HSTL15D_I	Differential HSTL 15 class I 4mA drive	0.32	0.69	1.06	ns
SSTL33_I	SSTL_3 class I	-0.25	0.05	0.35	ns
SSTL33_II	SSTL_3 class II	-0.31	-0.02	0.27	ns
SSTL33D_I	Differential SSTL_3 class I	-0.25	0.05	0.35	ns
SSTL33D_II	Differential SSTL_3 class II	-0.31	-0.02	0.27	ns
SSTL25_I	SSTL_2 class I 8mA drive	-0.25	0.02	0.30	ns
SSTL25_II	SSTL_2 class II 16mA drive	-0.28	0.00	0.28	ns
SSTL25D_I	Differential SSTL_2 class I 8mA drive	-0.25	0.02	0.30	ns
SSTL25D_II	Differential SSTL_2 class II 16mA drive	-0.28	0.00	0.28	ns
SSTL18_I	SSTL_1.8 class I	-0.17	0.13	0.43	ns
SSTL18_II	SSTL_1.8 class II 8mA drive	-0.18	0.12	0.42	ns
SSTL18D_I	Differential SSTL_1.8 class I	-0.17	0.13	0.43	ns
SSTL18D_II	Differential SSTL_1.8 class II 8mA drive	-0.18	0.12	0.42	ns
LVTTL33_4mA	LVTTL 4mA drive	-0.37	-0.05	0.26	ns
LVTTL33_8mA	LVTTL 8mA drive	-0.45	-0.18	0.10	ns
LVTTL33_12mA	LVTTL 12mA drive	-0.52	-0.24	0.04	ns
LVTTL33_16mA	LVTTL 16mA drive	-0.43	-0.14	0.14	ns
LVTTL33_20mA	LVTTL 20mA drive	-0.46	-0.18	0.09	ns
LVCMOS33_4mA	LVCMOS 3.3 4mA drive, fast slew rate	-0.37	-0.05	0.26	ns
LVCMOS33_8mA	LVCMOS 3.3 8mA drive, fast slew rate	-0.45	-0.18	0.10	ns
LVCMOS33_12mA	LVCMOS 3.3 12mA drive, fast slew rate	-0.52	-0.24	0.04	ns
LVCMOS33_16mA	LVCMOS 3.3 16mA drive, fast slew rate	-0.43	-0.14	0.14	ns
LVCMOS33_20mA	LVCMOS 3.3 20mA drive, fast slew rate	-0.46	-0.18	0.09	ns
LVCMOS25_4mA	LVCMOS 2.5 4mA drive, fast slew rate	-0.42	-0.15	0.13	ns
LVCMOS25_8mA	LVCMOS 2.5 8mA drive, fast slew rate	-0.48	-0.21	0.05	ns
LVCMOS25_12mA	LVCMOS 2.5 12mA drive, fast slew rate	0.00	0.00	0.00	ns
LVCMOS25_16mA	LVCMOS 2.5 16mA drive, fast slew rate	-0.45	-0.18	0.08	ns
LVCMOS25_20mA	LVCMOS 2.5 20mA drive, fast slew rate	-0.49	-0.22	0.04	ns
LVCMOS18_4mA	LVCMOS 1.8 4mA drive, fast slew rate	-0.46	-0.18	0.10	ns
LVCMOS18_8mA	LVCMOS 1.8 8mA drive, fast slew rate	-0.52	-0.25	0.02	ns
LVCMOS18_12mA	LVCMOS 1.8 12mA drive, fast slew rate	-0.56	-0.30	-0.03	ns
LVCMOS18_16mA	LVCMOS 1.8 16mA drive, fast slew rate	-0.50	-0.24	0.03	ns
LVCMOS15_4mA	LVCMOS 1.5 4mA drive, fast slew rate	-0.45	-0.17	0.11	ns
LVCMOS15_8mA	LVCMOS 1.5 8mA drive, fast slew rate	-0.53	-0.26	0.00	ns
LVCMOS12_2mA	LVCMOS 1.2 2mA drive, fast slew rate	-0.46	-0.19	0.08	ns
LVCMOS12_6mA	LVCMOS 1.2 6mA drive, fast slew rate	-0.55	-0.29	-0.02	ns
LVCMOS33_4mA	LVCMOS 3.3 4mA drive, slow slew rate	0.98	1.41	1.84	ns
LVCMOS33_8mA	LVCMOS 3.3 8mA drive, slow slew rate	0.74	1.16	1.58	ns
LVCMOS33_12mA	LVCMOS 3.3 12mA drive, slow slew rate	0.56	0.97	1.38	ns
LVCMOS33_16mA	LVCMOS 3.3 16mA drive, slow slew rate	0.77	1.19	1.61	ns
LVCMOS33_20mA	LVCMOS 3.3 20mA drive, slow slew rate	0.57	0.98	1.40	ns

LatticeXP2 Family Data Sheet
Pinout Information

February 2012 **Data Sheet DS1009**

Signal Descriptions

Signal Name	I/O	Description
General Purpose		
P[Edge] [Row/Column Number*]_[A/B]	I/O	[Edge] indicates the edge of the device on which the pad is located. Valid edge designations are L (Left), B (Bottom), R (Right), T (Top). [Row/Column Number] indicates the PFU row or the column of the device on which the PIC exists. When Edge is T (Top) or B (Bottom), only need to specify Row Number. When Edge is L (Left) or R (Right), only need to specify Column Number. [A/B] indicates the PIO within the PIC to which the pad is connected. Some of these user-programmable pins are shared with special function pins. These pins, when not used as special purpose pins, can be programmed as I/Os for user logic. During configuration the user-programmable I/Os are tri-stated with an internal pull-up resistor enabled. If any pin is not used (or not bonded to a package pin), it is also tri-stated with an internal pull-up resistor enabled after configuration.
GSRN	I	Global RESET signal (active low). Any I/O pin can be GSRN.
NC	—	No connect.
GND	—	Ground. Dedicated pins.
V_{CC}	—	Power supply pins for core logic. Dedicated pins.
V_{CCAUX}	—	Auxiliary power supply pin. This dedicated pin powers all the differential and referenced input buffers.
V_{CCPLL}	—	PLL supply pins. csBGA, PQFP and TQFP packages only.
V_{CCIOx}	—	Dedicated power supply pins for I/O bank x.
V_{REF1_x}, V_{REF2_x}	—	Reference supply pins for I/O bank x. Pre-determined pins in each bank are assigned as V_{REF} inputs. When not used, they may be used as I/O pins.
PLL and Clock Functions (Used as user programmable I/O pins when not in use for PLL or clock pins)		
[LOC][num]_V_{CCPLL}	—	Power supply pin for PLL: LLC, LRC, URC, ULC, num = row from center.
[LOC][num]_GPLL[T, C]_IN_A	I	General Purpose PLL (GPLL) input pads: LLC, LRC, URC, ULC, num = row from center, T = true and C = complement, index A,B,C...at each side.
[LOC][num]_GPLL[T, C]_FB_A	I	Optional feedback GPLL input pads: LLC, LRC, URC, ULC, num = row from center, T = true and C = complement, index A,B,C...at each side.
PCLK[T, C]_[n:0]_[3:0]	I	Primary Clock pads, T = true and C = complement, n per side, indexed by bank and 0,1,2,3 within bank.
[LOC]DQS[num]	I	DQS input pads: T (Top), R (Right), B (Bottom), L (Left), DQS, num = ball function number. Any pad can be configured to be output.
Test and Programming (Dedicated Pins)		
TMS	I	Test Mode Select input, used to control the 1149.1 state machine. Pull-up is enabled during configuration.
TCK	I	Test Clock input pin, used to clock the 1149.1 state machine. No pull-up enabled.
TDI	I	Test Data in pin. Used to load data into device using 1149.1 state machine. After power-up, this TAP port can be activated for configuration by sending appropriate command. (Note: once a configuration port is selected it is locked. Another configuration port cannot be selected until the power-up sequence). Pull-up is enabled during configuration.

Signal Descriptions (Cont.)

Signal Name	I/O	Description
TDO	O	Output pin. Test Data Out pin used to shift data out of a device using 1149.1.
VCCJ	—	Power supply pin for JTAG Test Access Port.
Configuration Pads (Used during sysCONFIG)		
CFG[1:0]	I	Mode pins used to specify configuration mode values latched on rising edge of INITN. During configuration, an internal pull-up is enabled.
INITN[1]	I/O	Open Drain pin. Indicates the FPGA is ready to be configured. During configuration, a pull-up is enabled.
PROGRAMN	I	Initiates configuration sequence when asserted low. This pin always has an active pull-up.
DONE	I/O	Open Drain pin. Indicates that the configuration sequence is complete, and the startup sequence is in progress.
CCLK	I/O	Configuration Clock for configuring an FPGA in sysCONFIG mode.
SISPI[2]	I/O	Input data pin in slave SPI mode and Output data pin in Master SPI mode.
SOSPI[2]	I/O	Output data pin in slave SPI mode and Input data pin in Master SPI mode.
CSSPIN[2]	O	Chip select for external SPI Flash memory in Master SPI mode. This pin has a weak internal pull-up.
CSSPISN	I	Chip select in Slave SPI mode. This pin has a weak internal pull-up.
TOE	I	Test Output Enable tristates all I/O pins when driven low. This pin has a weak internal pull-up, but when not used an external pull-up to V_{CC} is recommended.

1. If not actively driven, the internal pull-up may not be sufficient. An external pull-up resistor of 4.7k to 10kΩ is recommended.
2. When using the device in Master SPI mode, it must be mutually exclusive from JTAG operations (i.e. TCK tied to GND) or the JTAG TCK must be free-running when used in a system JTAG test environment. If Master SPI mode is used in conjunction with a JTAG download cable, the device power cycle is required after the cable is unplugged.

Pin Information Summary

Pin Type		XP2-5				XP2-8				XP2-17			XP2-30			XP2-40	
		132 csBGA	144 TQFP	208 PQFP	256 ftBGA	132 csBGA	144 TQFP	208 PQFP	256 ftBGA	208 PQFP	256 ftBGA	484 fpBGA	256 ftBGA	484 fpBGA	672 fpBGA	484 fpBGA	672 fpBGA
Single Ended User I/O		86	100	146	172	86	100	146	201	146	201	358	201	363	472	363	540
Differential Pair User I/O	Normal	35	39	57	66	35	39	57	77	57	77	135	77	137	180	137	204
	Highspeed	8	11	16	20	8	11	16	23	16	23	44	23	44	56	44	66
Configuration	TAP	5	5	5	5	5	5	5	5	5	5	5	5	5	5	5	5
	Muxed	9	9	9	9	9	9	9	9	9	9	9	9	9	9	9	9
	Dedicated	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1
Non Configuration	Muxed	5	5	7	7	7	7	9	9	11	11	21	7	11	13	11	13
	Dedicated	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1
Vcc		6	4	9	6	6	4	9	6	9	6	16	6	16	20	16	20
Vccaux		4	4	4	4	4	4	4	4	4	4	8	4	8	8	8	8
VCCPLL		2	2	2	-	2	2	2	-	4	-	-	-	-	-	-	-
VCCIO	Bank0	2	2	2	2	2	2	2	2	2	2	4	2	4	4	4	4
	Bank1	1	1	2	2	1	1	2	2	2	2	4	2	4	4	4	4
	Bank2	2	2	2	2	2	2	2	2	2	2	4	2	4	4	4	4
	Bank3	1	1	2	2	1	1	2	2	2	2	4	2	4	4	4	4
	Bank4	1	1	2	2	1	1	2	2	2	2	4	2	4	4	4	4
	Bank5	2	2	2	2	2	2	2	2	2	2	4	2	4	4	4	4
	Bank6	1	1	2	2	1	1	2	2	2	2	4	2	4	4	4	4
	Bank7	2	2	2	2	2	2	2	2	2	2	4	2	4	4	4	4
GND, GND0-GND7		15	15	20	20	15	15	22	20	22	20	56	20	56	64	56	64
NC		-	-	4	31	-	-	2	2	-	2	7	2	2	69	2	1
Single Ended/ Differential I/O per Bank	Bank0	18/9	20/10	20/10	26/13	18/9	20/10	20/10	28/14	20/10	28/14	52/26	28/14	52/26	70/35	52/26	70/35
	Bank1	4/2	6/3	18/9	18/9	4/2	6/3	18/9	22/11	18/9	22/11	36/18	22/11	36/18	54/27	36/18	70/35
	Bank2	16/8	18/9	18/9	22/11	16/8	18/9	18/9	26/13	18/9	26/13	46/23	26/13	46/23	56/28	46/23	64/32
	Bank3	4/2	4/2	16/8	20/10	4/2	4/2	16/8	24/12	16/8	24/12	44/22	24/12	46/23	56/28	46/23	66/33
	Bank4	8/4	8/4	18/9	18/9	8/4	8/4	18/9	26/13	18/9	26/13	36/18	26/13	38/19	54/27	38/19	70/35
	Bank5	14/7	18/9	20/10	24/12	14/7	18/9	20/10	24/12	20/10	24/12	52/26	24/12	53/26	70/35	53/26	70/35
	Bank6	6/3	8/4	18/9	22/11	6/3	8/4	18/9	27/13	18/9	27/13	46/23	27/13	46/23	56/28	46/23	66/33
	Bank7	16/8	18/9	18/9	22/11	16/8	18/9	18/9	24/12	18/9	24/12	46/23	24/12	46/23	56/28	46/23	64/32
True LVDS Pairs Bonding Out per Bank	Bank0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank2	3	4	4	5	3	4	4	6	4	6	11	6	11	14	11	16
	Bank3	1	1	4	5	1	1	4	6	4	6	11	6	11	14	11	17
	Bank4	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank5	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank6	1	2	4	5	1	2	4	6	4	6	11	6	11	14	11	17
	Bank7	3	4	4	5	3	4	4	5	4	5	11	5	11	14	11	16
DDR Banks Bonding Out per I/O Bank[1]	Bank0	1	1	1	1	1	1	1	1	1	1	3	1	2	4	2	4
	Bank1	0	0	1	1	0	0	1	1	1	1	2	1	2	3	2	4
	Bank2	1	1	1	1	1	1	1	1	1	1	2	1	3	3	3	4
	Bank3	0	0	1	1	0	0	1	1	1	1	2	1	3	3	3	4
	Bank4	0	0	1	1	0	0	1	1	1	1	2	1	2	3	2	4
	Bank5	1	1	1	1	1	1	1	1	1	1	3	1	2	4	2	4
	Bank6	0	0	1	1	0	0	1	1	1	1	2	1	3	3	3	4
	Bank7	1	1	1	1	1	1	1	1	1	1	2	1	3	3	3	4

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-30E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	30
LFXP2-30E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	30
LFXP2-30E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	30
LFXP2-30E-5FN484C	1.2V	-5	Lead-Free fpBGA	484	COM	30
LFXP2-30E-6FN484C	1.2V	-6	Lead-Free fpBGA	484	COM	30
LFXP2-30E-7FN484C	1.2V	-7	Lead-Free fpBGA	484	COM	30
LFXP2-30E-5FN672C	1.2V	-5	Lead-Free fpBGA	672	COM	30
LFXP2-30E-6FN672C	1.2V	-6	Lead-Free fpBGA	672	COM	30
LFXP2-30E-7FN672C	1.2V	-7	Lead-Free fpBGA	672	COM	30

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-40E-5FN484C	1.2V	-5	Lead-Free fpBGA	484	COM	40
LFXP2-40E-6FN484C	1.2V	-6	Lead-Free fpBGA	484	COM	40
LFXP2-40E-7FN484C	1.2V	-7	Lead-Free fpBGA	484	COM	40
LFXP2-40E-5FN672C	1.2V	-5	Lead-Free fpBGA	672	COM	40
LFXP2-40E-6FN672C	1.2V	-6	Lead-Free fpBGA	672	COM	40
LFXP2-40E-7FN672C	1.2V	-7	Lead-Free fpBGA	672	COM	40

Industrial

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-5E-5MN132I	1.2V	-5	Lead-Free csBGA	132	IND	5
LFXP2-5E-6MN132I	1.2V	-6	Lead-Free csBGA	132	IND	5
LFXP2-5E-5TN144I	1.2V	-5	Lead-Free TQFP	144	IND	5
LFXP2-5E-6TN144I	1.2V	-6	Lead-Free TQFP	144	IND	5
LFXP2-5E-5QN208I	1.2V	-5	Lead-Free PQFP	208	IND	5
LFXP2-5E-6QN208I	1.2V	-6	Lead-Free PQFP	208	IND	5
LFXP2-5E-5FTN256I	1.2V	-5	Lead-Free ftBGA	256	IND	5
LFXP2-5E-6FTN256I	1.2V	-6	Lead-Free ftBGA	256	IND	5

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-8E-5MN132I	1.2V	-5	Lead-Free csBGA	132	IND	8
LFXP2-8E-6MN132I	1.2V	-6	Lead-Free csBGA	132	IND	8
LFXP2-8E-5TN144I	1.2V	-5	Lead-Free TQFP	144	IND	8
LFXP2-8E-6TN144I	1.2V	-6	Lead-Free TQFP	144	IND	8
LFXP2-8E-5QN208I	1.2V	-5	Lead-Free PQFP	208	IND	8
LFXP2-8E-6QN208I	1.2V	-6	Lead-Free PQFP	208	IND	8
LFXP2-8E-5FTN256I	1.2V	-5	Lead-Free ftBGA	256	IND	8
LFXP2-8E-6FTN256I	1.2V	-6	Lead-Free ftBGA	256	IND	8